# 8-Bit Serial or Parallel-Input/ Serial-Output Shift Register High-Performance Silicon-Gate CMOS

# MC74HC165A

The MC74HC165A is identical in pinout to the LS165. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is an 8-bit shift register with complementary outputs from the last stage. Data may be loaded into the register either in parallel or in serial form. When the Serial Shift/Parallel Load input is low, the data is loaded asynchronously in parallel. When the Serial Shift/Parallel Load input is high, the data is loaded serially on the rising edge of either Clock or Clock Inhibit (see the Function Table).

The 2-input NOR clock may be used either by combining two independent clock sources or by designating one of the clock inputs to act as a clock inhibit.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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#### MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





QFN16 MN SUFFIX CASE 485AW



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

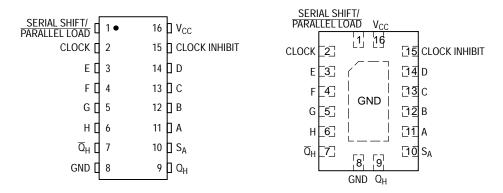


Figure 1. Pin Assignments

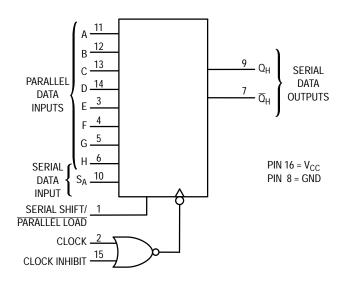


Figure 2. Logic Diagram

#### **FUNCTION TABLE**

	lr	nputs			Internal Stages C		Output	
Serial Shift/ Parallel Load	Clock	Clock Inhibit	S <sub>A</sub>	A – H	Q <sub>A</sub>	$Q_{B}$	Q <sub>H</sub>	Operation
L	Х	Х	Х	a h	а	b	h	Asynchronous Parallel Load
H H	\( \sigma \)	L L	L H	X X	L H	Q <sub>An</sub> Q <sub>An</sub>	Q <sub>Gn</sub> Q <sub>Gn</sub>	Serial Shift via Clock
H H	L L	<i></i>	L H	X X	L H	Q <sub>An</sub> Q <sub>An</sub>	Q <sub>Gn</sub> Q <sub>Gn</sub>	Serial Shift via Clock Inhibit
H H	X H	H X	X X	X X	No Change			Inhibited Clock
Н	L	L	Х	Х		No Change		No Clock

X = don't care  $Q_{An} - Q_{Gn} = Data shifted from the preceding stage$ 

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C SOIC Package: – 7 mW/°C from 65° to 125°C

TSSOP Package: – 7 mW/°C from 65° to 125°C

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND	2.0	6.0	V	
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Refer GND)	0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature, All Package Typ	es	<b>- 55</b>	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	all Time $ \begin{array}{c} V_{CC} = 2.0 \text{ V} \\ V_{CC} = 3.0 \text{ V} \\ V_{CC} = 4.5 \text{ V} \\ V_{CC} = 6.0 \text{ V} \end{array} $		1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			v <sub>cc</sub>	Gua	ranteed Limi	it	
Symbol	Parameter	Test Conditions	v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\label{eq:Vin} \begin{array}{c c} V_{in} = V_{IH} \text{ or } V_{IL} &  I_{out}  \leq 2.4 \text{ mA} \\ &  I_{out}  \leq 4.0 \text{ mA} \\ &  I_{out}  \leq 5.2 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	V

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			V <sub>CC</sub> Guaranteed Limit				
Symbol	Parameter	Test Conditions	٧	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{in} = V_{IH} \text{ or } V_{IL} &   I_{out}  \leq 2.4 \text{ mA} \\ &   I_{out}  \leq 4.0 \text{ mA} \\ &   I_{out}  \leq 5.2 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I <sub>in</sub>	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# AC ELECTRICAL CHARACTERISTICS (C $_L$ = 50 pF, Input $t_{\rm f}$ = $t_{\rm f}$ = 6 ns)

			Guaranteed Limit			
Symbol	Parameter	v <sub>cc</sub>	– 55 to 25°C	°C ≤ 85°C ≤ 125°C		Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 8)	2.0 3.0 4.5 6.0	6 18 30 35	4.8 17 24 28	4 15 20 24	MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Clock (or Clock Inhibit) to $Q_{H}$ or $\overline{Q}_{H}$ (Figures 1 and 8)	2.0 3.0 4.5 6.0	150 52 30 26	190 63 38 33	225 65 45 38	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Serial Shift/Parallel Load to $Q_H$ or $\overline{Q}_H$ (Figures 2 and 8)	2.0 3.0 4.5 6.0	175 58 35 30	220 70 44 37	265 72 53 45	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input H to $Q_H$ or $\overline{Q}_H$ (Figures 3 and 8)	2.0 3.0 4.5 6.0	150 52 30 26	190 63 38 33	225 65 45 38	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 8)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Package)*	40	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

### **TIMING REQUIREMENTS** (Input $t_r = t_f = 6 \text{ ns}$ )

		Vcc	Guar	anteed Lim	it	
Symbol	Parameter	V	– 55 to 25°C	≤ <b>85</b> ° <b>C</b>	≤ 125°C	Unit
t <sub>su</sub>	Minimum Setup Time, Parallel Data Inputs to Serial Shift/Parallel Load	2.0	75	95	110	ns
Su	(Figure 4)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>su</sub>	Minimum Setup Time, Input SA to Clock (or Clock Inhibit)	2.0	75	95	110	ns
Su	(Figure 5)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>su</sub>	Minimum Setup Time, Serial Shift/Parallel Load to Clock (or Clock Inhibit)	2.0	75	95	110	ns
Su	(Figure 6)	3.0	30	40	55	
	(1.194.10-0)	4.5	15	19	22	
		6.0	13	16	19	
t <sub>su</sub>	Minimum Setup Time, Clock to Clock Inhibit	2.0	75	95	110	ns
•su	(Figure 7)	3.0	30	40	55	110
	(Figure 7)	4.5	15	19	22	
		6.0	13	16	19	
t.	Minimum Hold Time, Serial Shift/Parallel Load to Parallel Data Inputs	2.0	5	5	5	ns
t <sub>h</sub>	(Figure 4)	3.0	5	5	5	113
	(Figure 4)	4.5	5	5	5	
		6.0	5	5	5	
	Military Charles (All Charles (					
t <sub>h</sub>	Minimum Hold Time, Clock (or Clock Inhibit) to Input SA	2.0	5	5	5	ns
	(Figure 5)	3.0	5	5	5	
		4.5 6.0	5 5	5 5	5 5	
t <sub>h</sub>	Minimum Hold Time, Clock (or Clock Inhibit) to Serial Shift/Parallel Load	2.0	5	5	5	ns
	(Figure 6)	3.0	5	5	5	
		4.5	5	5	5	
		6.0	5	5	5	
$t_{rec}$	Minimum Recovery Time, Clock to Clock Inhibit	2.0	75	95	110	ns
	(Figure 7)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>w</sub>	Minimum Pulse Width, Clock (or Clock Inhibit)	2.0	70	90	100	ns
	(Figure 1)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>w</sub>	Minimum Pulse width, Serial Shift/Parallel Load	2.0	70	90	100	ns
••	(Figure 2)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times	2.0	1000	1000	1000	ns
	(Figure 1)	3.0	800	800	800	
		4.5	500	500	500	
		6.0	400	400	400	

#### PIN DESCRIPTIONS

#### **INPUTS**

#### A, B, C, D, E, F, G, H (Pins 11, 12, 13, 14, 3, 4, 5, 6)

Parallel Data inputs. Data on these inputs are asynchronously entered in parallel into the internal flip-flops when the Serial Shift/Parallel Load input is low.

#### **SA (Pin 10)**

Serial Data input. When the Serial Shift/Parallel Load input is high, data on this pin is serially entered into the first stage of the shift register with the rising edge of the Clock.

#### **CONTROL INPUTS**

#### Serial Shift/Parallel Load (Pin 1)

Data-entry control input. When a high level is applied to this pin, data at the Serial Data input (SA) are shifted into the register with the rising edge of the Clock. When a low level is applied to this pin, data at the Parallel Data inputs are asynchronously loaded into each of the eight internal stages.

#### Clock, Clock Inhibit (Pins 2, 15)

Clock inputs. These two clock inputs function identically. Either may be used as an active-high clock inhibit. However, to avoid double clocking, the inhibit input should go high only while the clock input is high.

The shift register is completely static, allowing Clock rates down to DC in a continuous or intermittent mode.

#### **OUTPUTS**

# $Q_H, \overline{Q}_H$ (Pins 9, 7)

Complementary Shift Register outputs. These pins are the noninverted and inverted outputs of the eighth stage of the shift register.

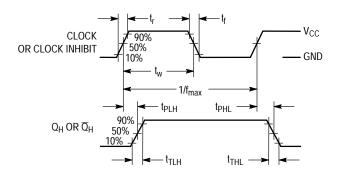
#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>		
MC74HC165ANG	PDIP-16 (Pb-Free)	500 Units / Rail		
MC74HC165ADG		48 Units / Rail		
MC74HC165ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel		
NLV74HC165ADR2G*	(15 1100)	2500 Units / Reel		
MC74HC165ADTR2G	TSSOP-16	2500 Units / Reel		
NLV74HC165ADTR2G*	(Pb-Free)	2500 Units / Reel		
MC74HC165AMNTWG	QFN16	3000 Units / Reel		
MC74HC165AMN2TWG	(Pb-Free)	3000 Units / Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

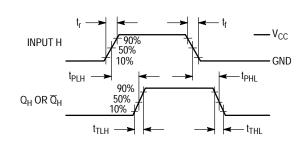
#### **SWITCHING WAVEFORMS**



SERIAL SHIFT/
PARALLEL LOAD  $V_{CC}$   $V_{CC}$ 

Figure 3. Serial-Shirt Mode

Figure 4. Parallel-Load Mode



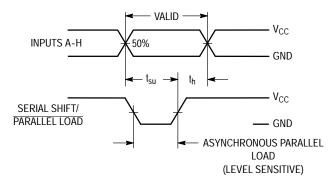
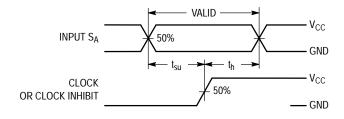


Figure 5. Parallel-Load Mode

Figure 6. Parallel-Load Mode



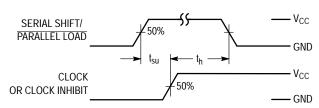
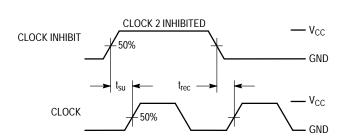


Figure 7. Serial-Shift Mode

Figure 8. Serial-Shift Mode



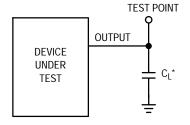
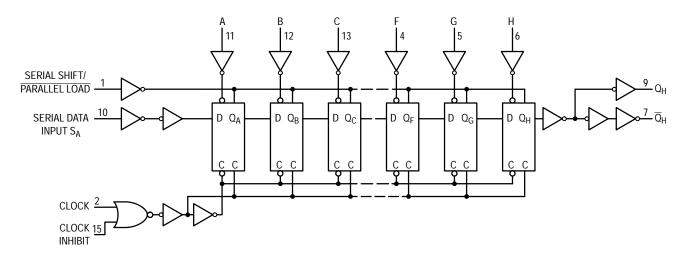


Figure 9. Serial-Shift, Clock-Inhibit Mode

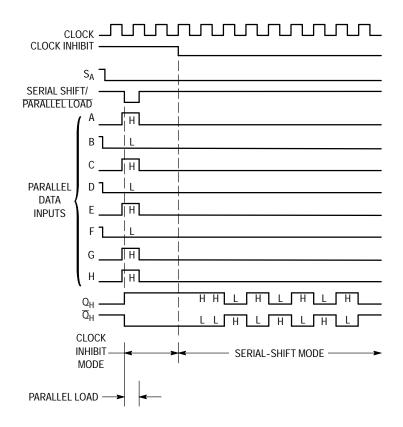
\*Includes all probe and jig capacitance

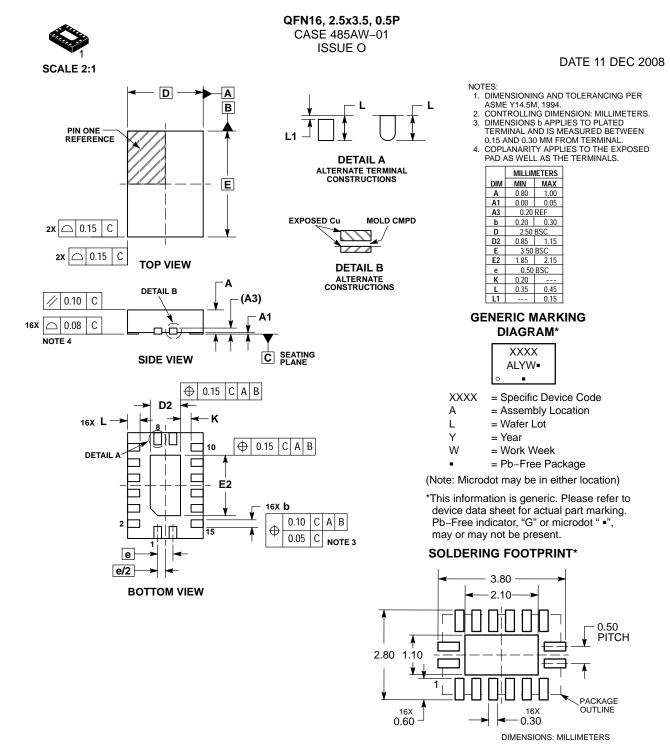
Figure 10. Test Circuit

#### **EXPANDED LOGIC DIAGRAM**



#### **TIMING DIAGRAM**

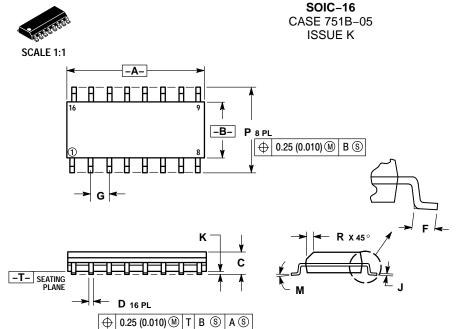




\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MIN MAX MIN		MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

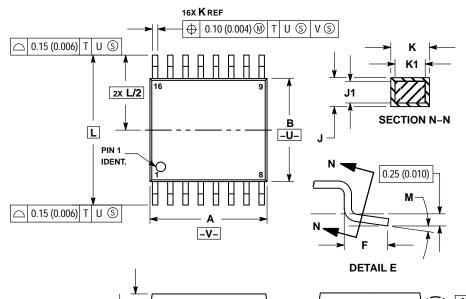
STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	COL DEDINO	FOOTDDINT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTPRINT
15.	EMITTER	15.	ANODE	15.		15.	BASE, #1	s	ЗX
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		40
					,		,	0.	40
OT) // E =		077/15 0		OT) (1 F =					16X 1.12
STYLE 5:	DDAIN DVE #4	STYLE 6:	OATHODE	STYLE 7:	SOURCE N-CH				10X 1.12   4 P
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.		-			16
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPUT			ا لــــا ل	10
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPUT	1)		<u> </u>	
4.	DRAIN, #2	4.		4.	GATE P-CH	-		<u> </u>	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT		_16	5X 1	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT		0.5	58	i <u>L</u>
7.	DRAIN, #4	7.		7.	COMMON DRAIN (OUTPUT	1)			<u> </u>
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH				
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH	-			<del></del>
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT				
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.		12.	COMMON DRAIN (OUTPUT	1)			
13.	GATE, #2	13.		13.	GATE N-CH	_			
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPU				i PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT	I)			
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								<b></b> 8	9 <del>L</del>
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									DIMENSIONS: MILLIMETERS
									DIVILINGIONS. WILLINETERS

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**DATE 19 OCT 2006** 



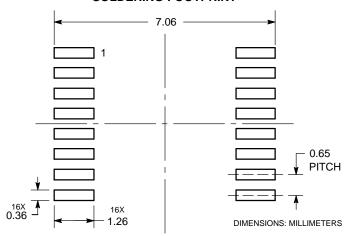
#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- ANSI 114.5M, 1962. CONTROLLING DIMENSION: MILLIMETER. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Г	6.40 BSC		0.252 BSC	
М	0 °	8°	0 °	8 °

#### **SOLDERING FOOTPRINT**

G



#### **GENERIC MARKING DIAGRAM\***

XXXX XXXX **ALYW** 1<del>88888888</del>

= Specific Device Code XXXX = Assembly Location Α = Wafer Lot Υ = Year W = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■",

= Pb-Free Package

may or may not be present.

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☐ 0.10 (0.004)

D.

-T- SEATING PLANE

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